JJMICROELECTRONICS

-60V, -7.8A, 26mΩ P-channel MOSFET

JMPL0625AP

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔVds Tested
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

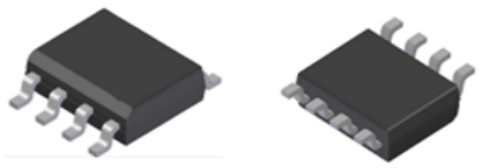
- Load Switch
- PWM Application
- Power Management

Product Summary

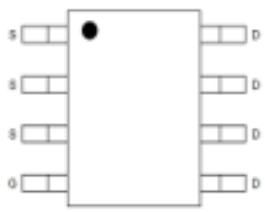
Parameters	Value	Unit
V_{DSS}	-60	V
$V_{GS(th)\_Typ}$	-1.9	V
I_D(@V_{GS}=10V)	-7.8	A
$R_{DS(ON)\_Typ}$(@V_{GS}=-10V	20	mΩ
$R_{DS(ON)\_Typ}$(@V_{GS}=-4.5V	26	mΩ

RoHS

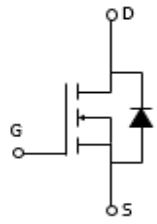
Pb Lead-free Green



SOP-8



Pin Assignment



Schematic

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMPL0625AP	PL0625A	3	Tape&Reel	SOP-8	4000	40000

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		-60	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_A = 25°C	-7.8	A
		T_A = 100°C	-4.9	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		165	mJ
P_D	Power Dissipation	T_A = 25°C	2.1	W
		T_A = 100°C	0.8	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	61	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(4)	60	

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = -250μA, V_{GS} = 0V	-60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -48V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250μA	-1.3	-1.9	-2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(5)	V_{GS} = -10V, I_D = -10A	-	20	25	mΩ
		V_{GS} = -4.5V, I_D = -7A	-	26	34	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	4.4	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = -30V, f = 1MHz	1159	1623	2191	pF
C_{oss}	Output Capacitance		286	400	541	pF
C_{rss}	Reverse Transfer Capacitance		10	14	19	pF
Q_g	Total Gate Charge	V_{GS} = 0 to -4.5V V_{DS} = -30V, I_D = -7A	18	25	34	nC
Q_{gs}	Gate Source Charge		-	6.5	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	3.3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = -10V, V_{DD} = -30V I_D= -7A, R_{GEN} = 3Ω	-	7.5	-	ns
t_r	Turn-On Rise Time		-	4.2	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	30	-	ns
t_f	Turn-Off Fall Time		-	5.7	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	-7.8	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	-31	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = -10A	-		-1.2	V
trr	Body Diode Reverse Recovery Time	I_F = -7A, di/dt = 100A/us	-	37	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	40	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25C, V_{DD}=-30V, V_G=-10V, R_G=25ohm, L=3mH, I_{AS}=-10.5A, V_{DD}=0V during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a minimum recommended pad of 2oz copper FR4 PCB.
4. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
5. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Power De-rating

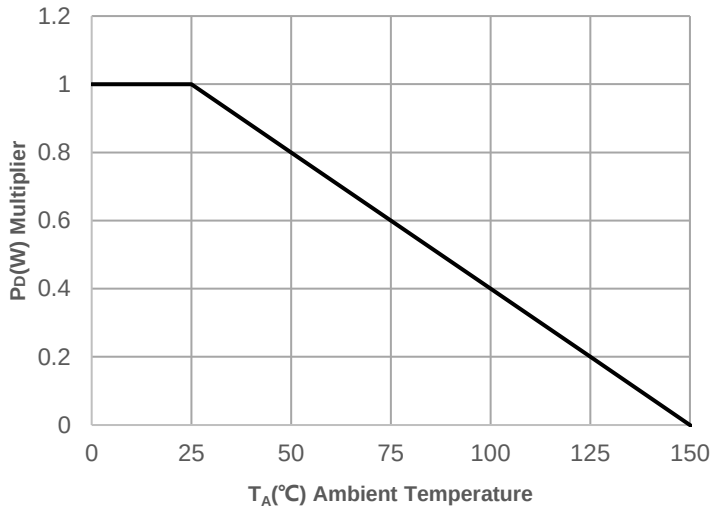


Figure 2: Current De-rating

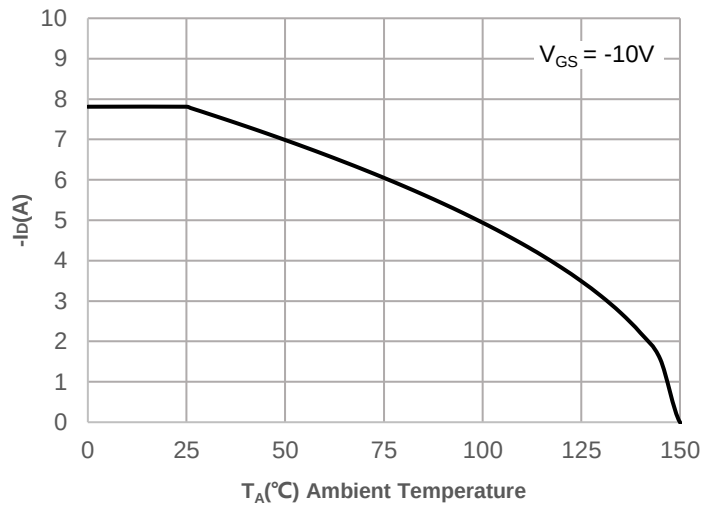


Figure 3: Normalized Maximum Transient Thermal Impedance

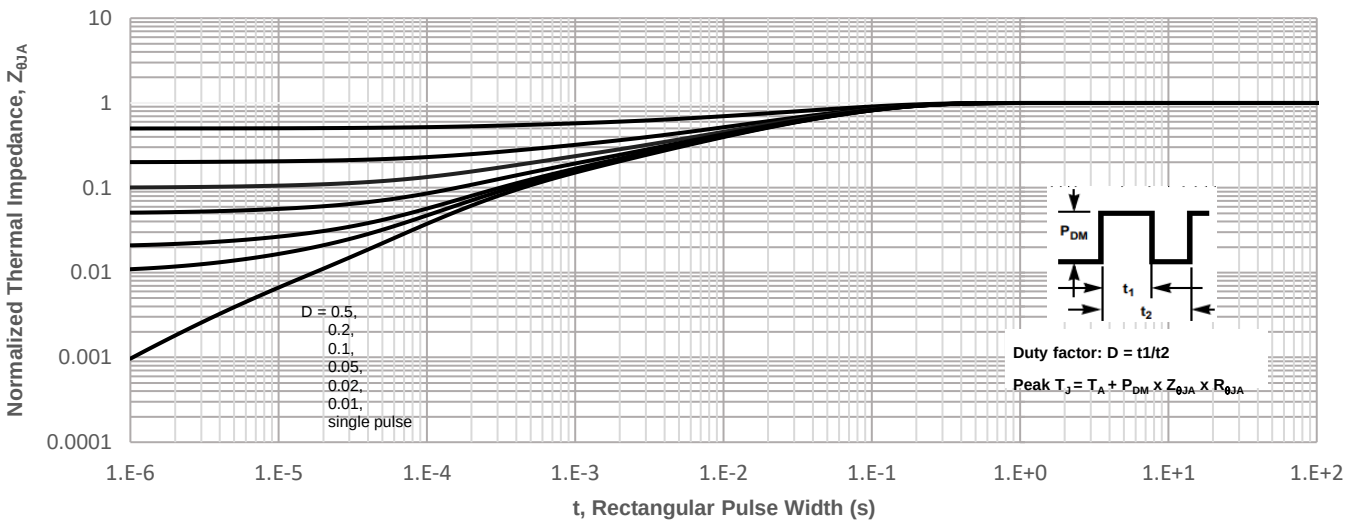
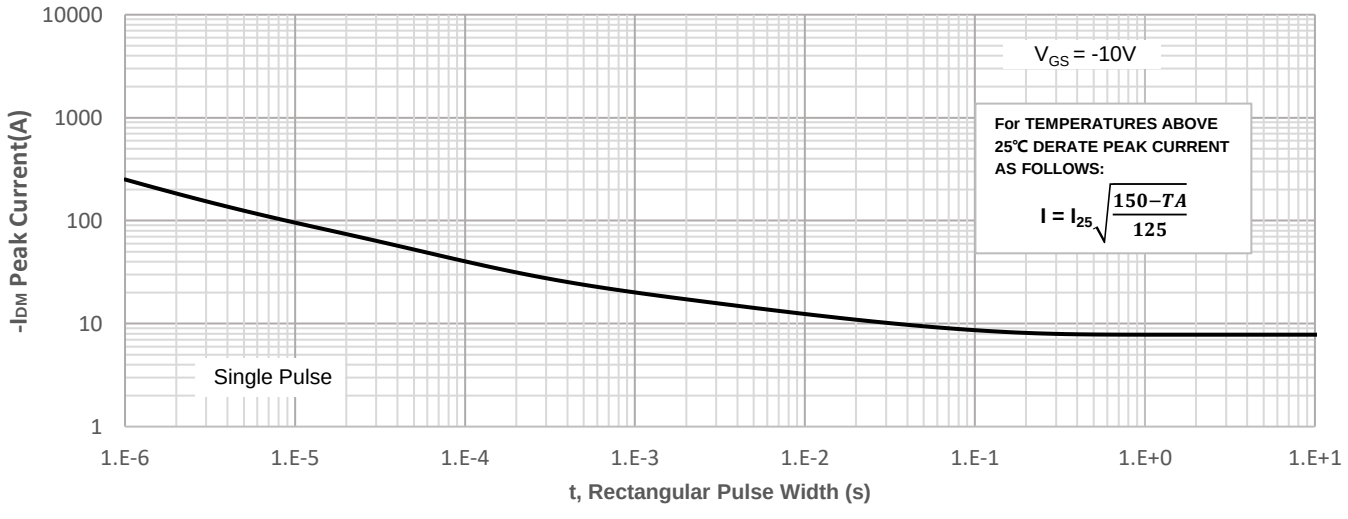


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

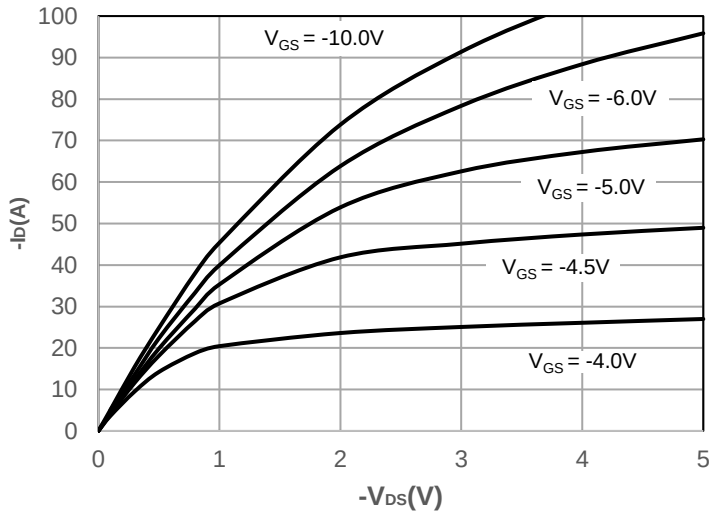


Figure 6: Typical Transfer Characteristics

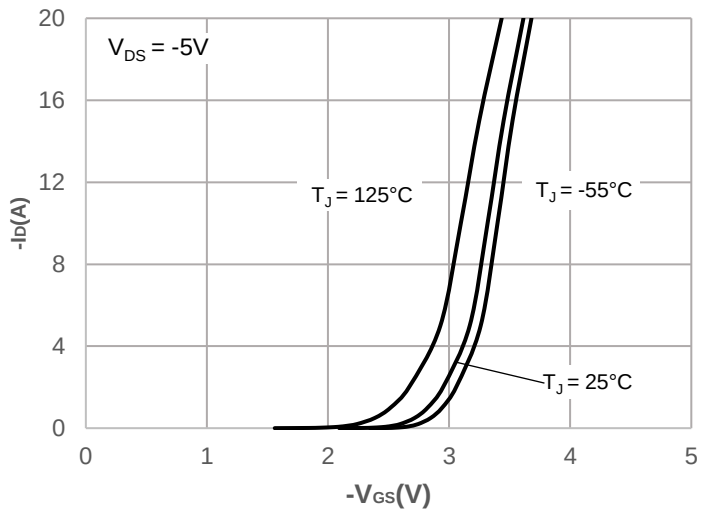


Figure 7: On-resistance vs. Drain Current

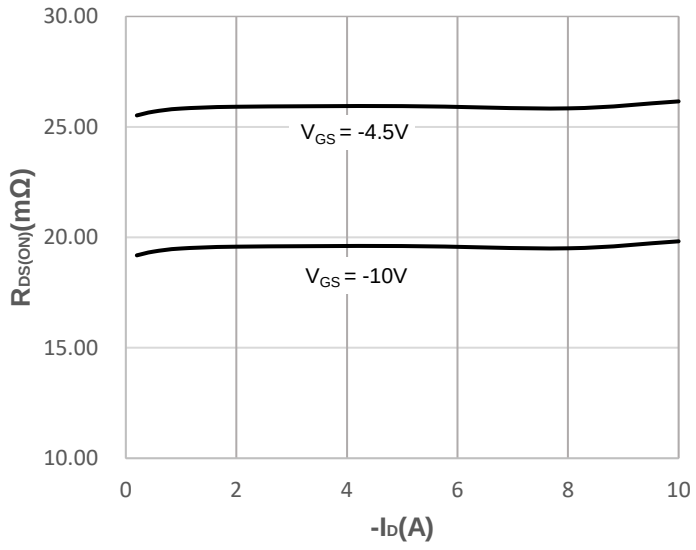


Figure 8: Body Diode Characteristics

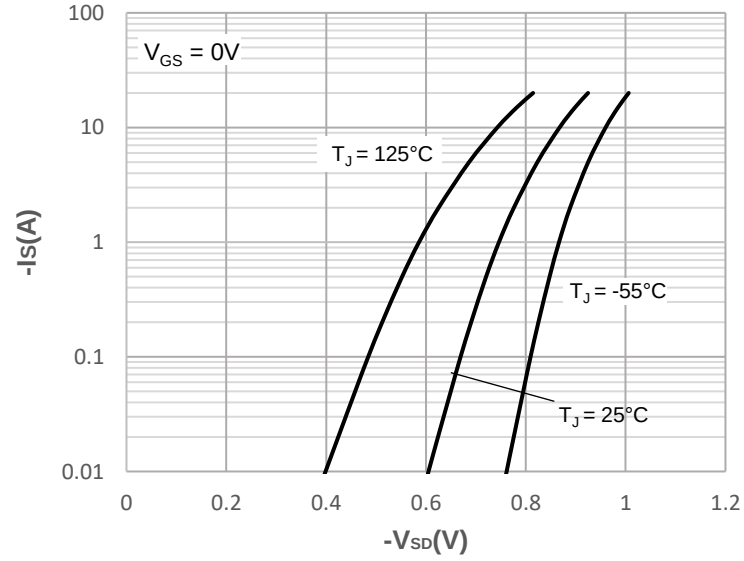


Figure 9: Gate Charge Characteristics

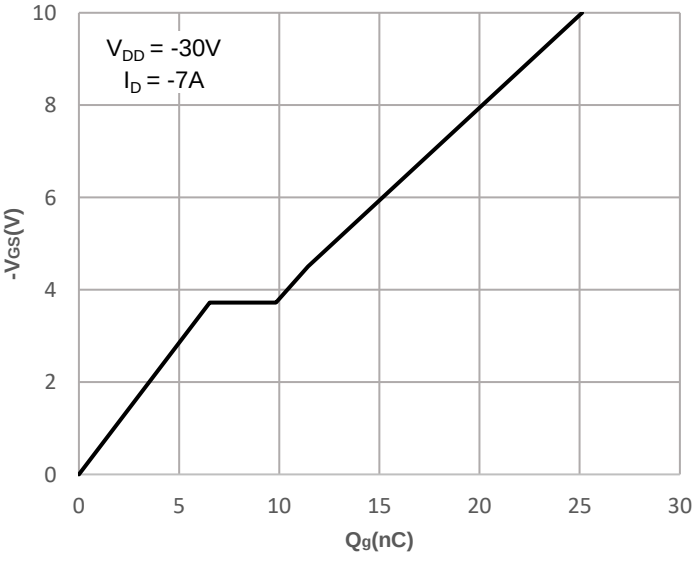
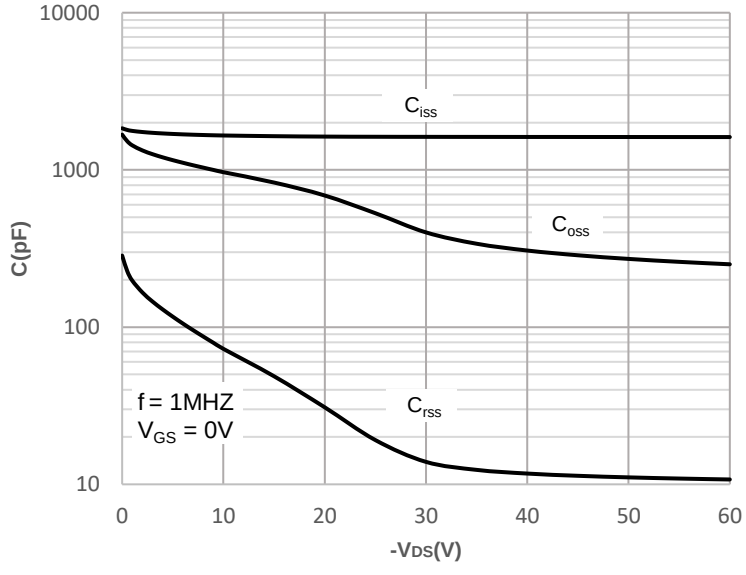


Figure 10: Capacitance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

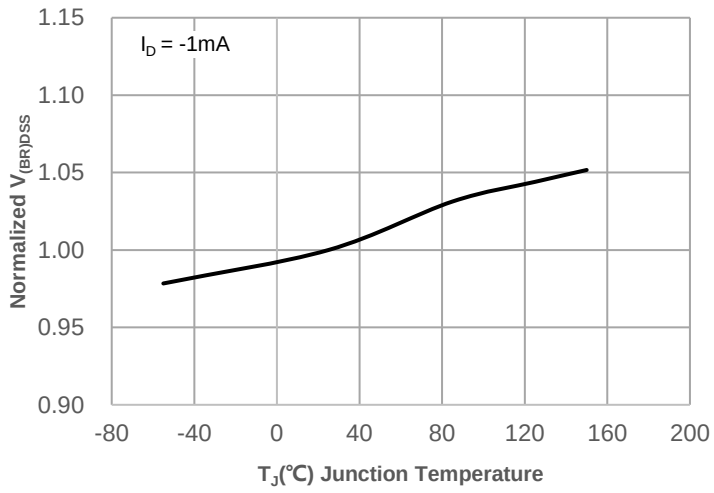


Figure 12: Normalized on Resistance vs. Junction Temperature

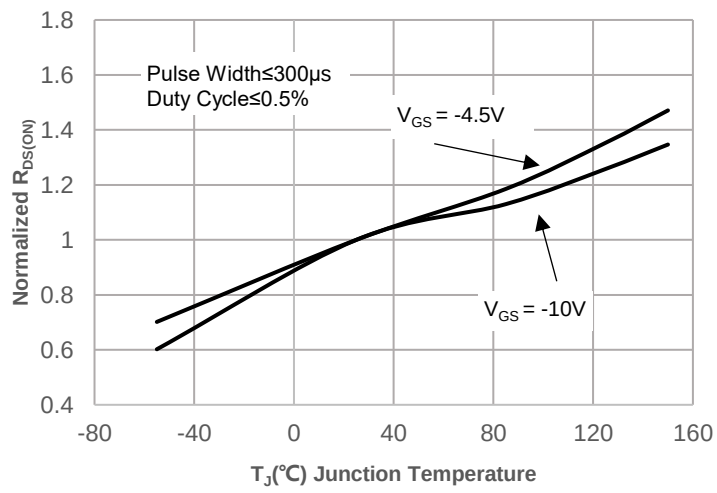


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

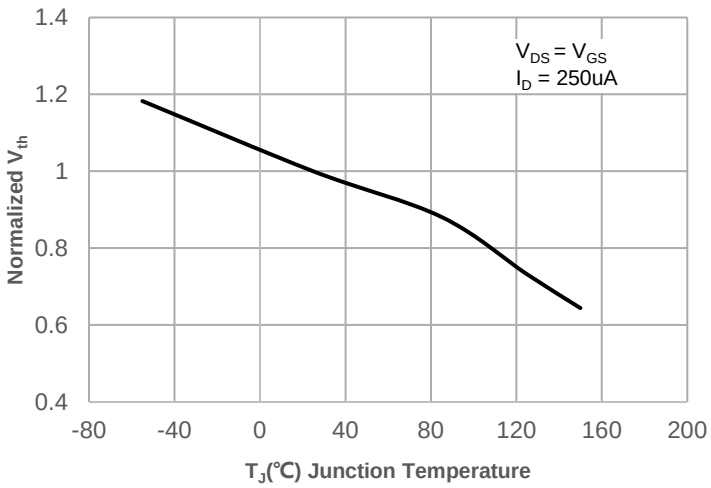


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

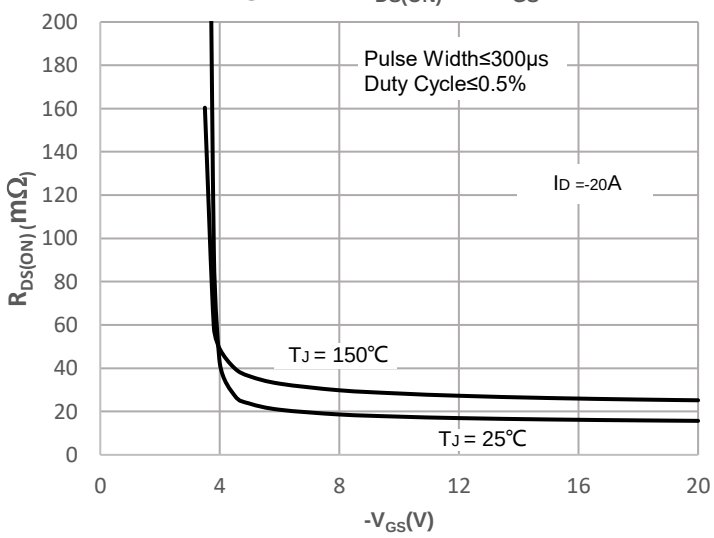
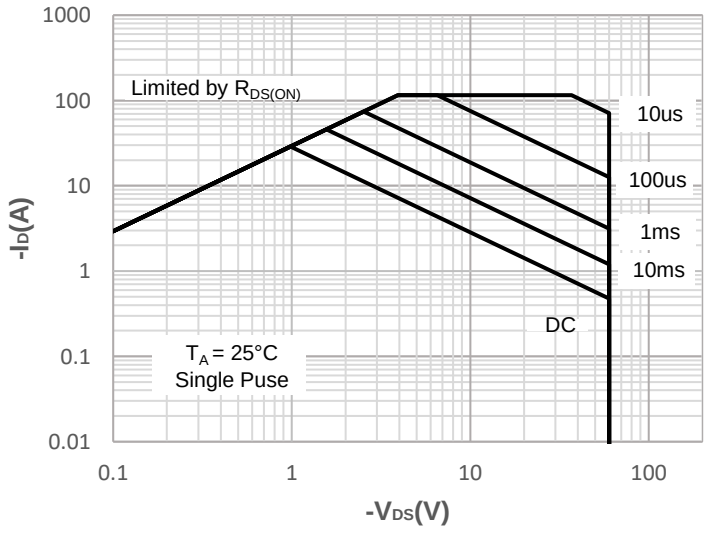


Figure 15: Maximum Safe Operating Area



Test Circuit

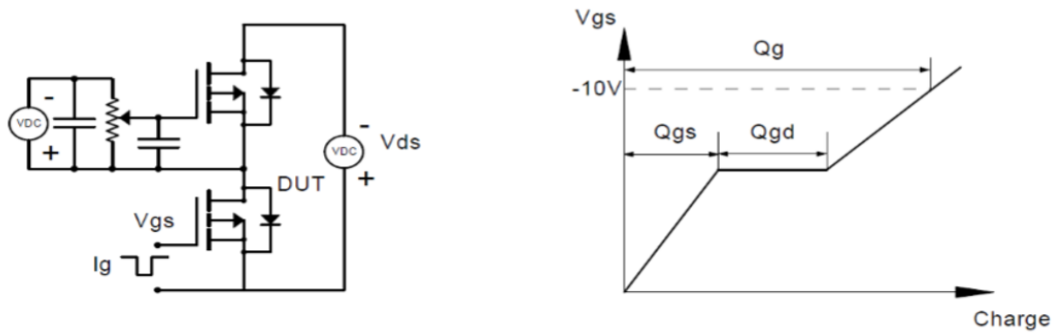


Figure 1: Gate Charge Test Circuit & Waveform

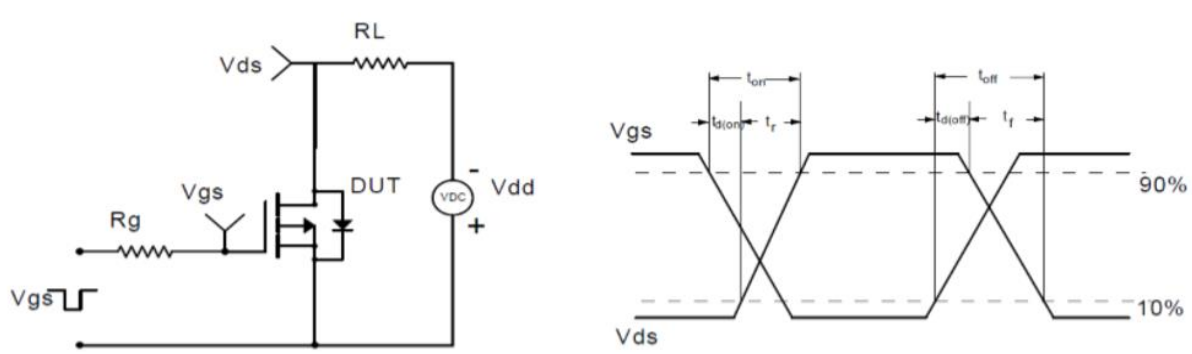


Figure 2: Resistive Switching Test Circuit & Waveform

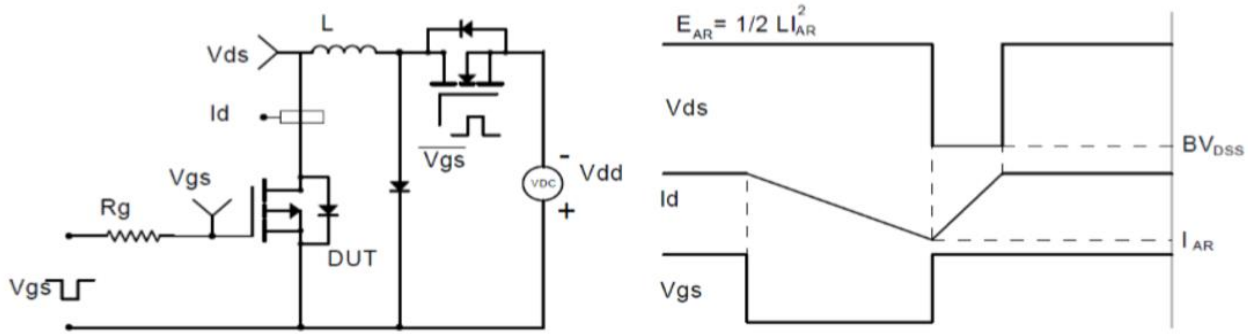


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

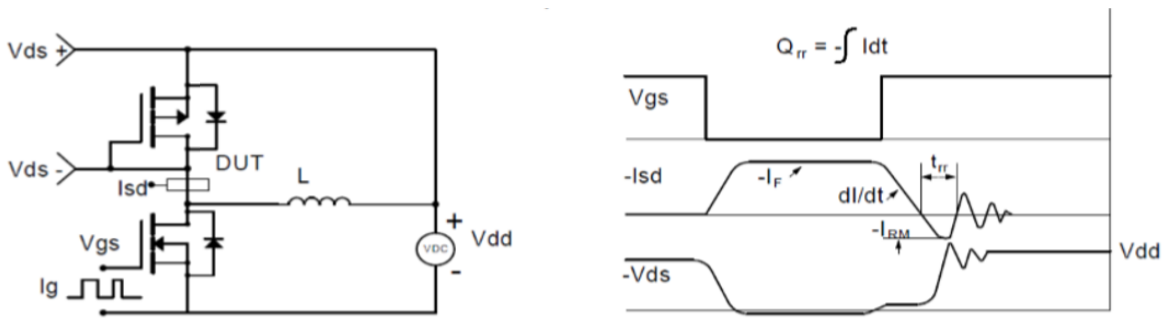
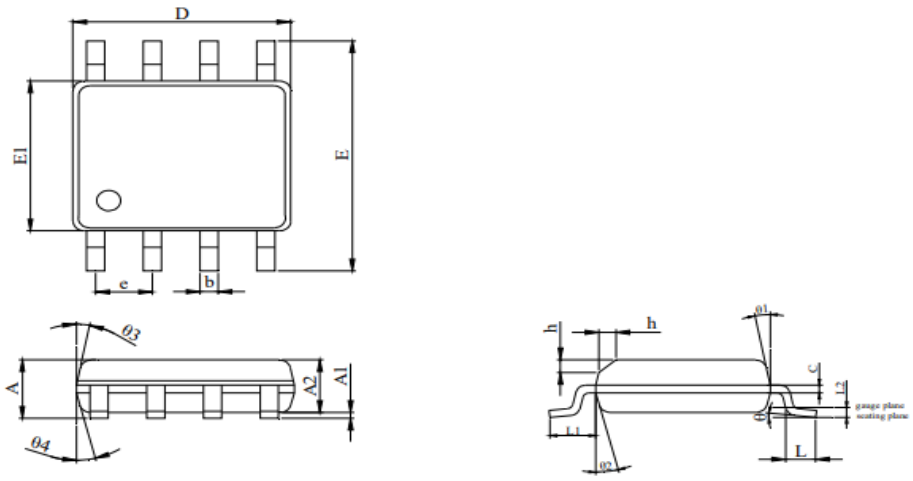


Figure 4: Diode Recovery Test Circuit & Waveform

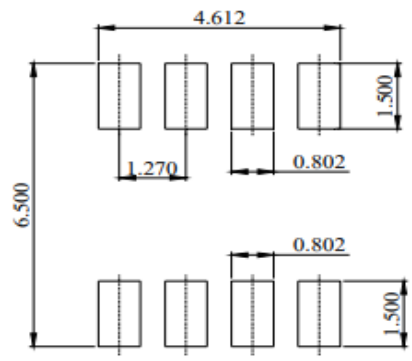
Package Mechanical Data(SOP-8)

Package Outline



DIM	MILLIMETER		
	MIN.	NOM.	MAX.
A	1.35	1.50	1.65
A1	0.05	0.10	0.15
A2	1.35	1.40	1.50
b	0.38	--	0.50
c	0.17	--	0.25
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.27(BSC)		
L	0.45	0.60	0.80
L1	1.04 REF		
L2	0.25 BSC		
h	0.30	0.40	0.50
θ	0°	--	8°
θ_1	10°	12°	14°
θ_2	8°	10°	12°
θ_3	10°	12°	14°
θ_4	8°	10°	12°

Recommended Footprint



DIMENSIONS:MILLIMETERS